

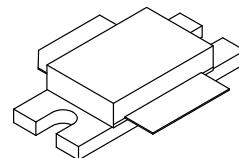
The RF Sub-Micron Bipolar Line RF Power Bipolar Transistors

Designed for broadband commercial and industrial applications at frequencies from 1400 to 1600 MHz. The high gain and broadband performance of these devices makes them ideal for large-signal, common-emitter class A and class AB amplifier applications in 26 volt amplitude modulated and multi-carrier base station equipment.

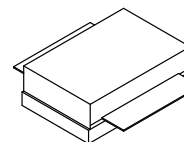
- Guaranteed Two-Tone Performance at 1490 MHz, 26 Volts
Output Power — 60 Watts (PEP)
Power Gain — 10 dB
Efficiency — 33%
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- S-Parameter Characterization at High Bias Levels
- Excellent Thermal Stability
- All Gold Metal for Ultra Reliability
- Capable of Handling 3:1 VSWR @ 26 Vdc, 1490 MHz, 60 Watts (PEP)
Output Power

MRF15060
MRF15060S

60 W, 1.49 GHz
RF POWER
BIPOLAR
TRANSISTORS



CASE 451-04, STYLE 1
(MRF15060)



CASE 451A-01, STYLE 1
(MRF15060S)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Emitter Voltage	V_{CES}	60	Vdc
Emitter-Base Voltage	V_{EBO}	60	Adc
Collector Current – Continuous	I_C	8	Adc
Total Device Dissipation @ $T_C = 70^\circ\text{C}$ Derate above 70°C	P_D	185 1.43	Watts W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	– 65 to +150	$^\circ\text{C}$
Operating Junction Temperature	T_J	200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.7	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 50\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	25	—	—	Vdc
Collector–Emitter Breakdown Voltage ($I_C = 50\text{ mA}$, $V_{BE} = 0$)	$V_{(BR)CES}$	60	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10\text{ mA}$, $I_C = 0\text{ mA}$)	$V_{(BR)EBO}$	3	3.5	—	Vdc
Collector Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $V_{BE} = 0$)	I_{CES}	—	—	10	mA

ON CHARACTERISTICS

DC Current Gain ($I_C = 1\text{ A}$, $V_{CE} = 5\text{ Vdc}$)	h_{FE}	20	40	80	—
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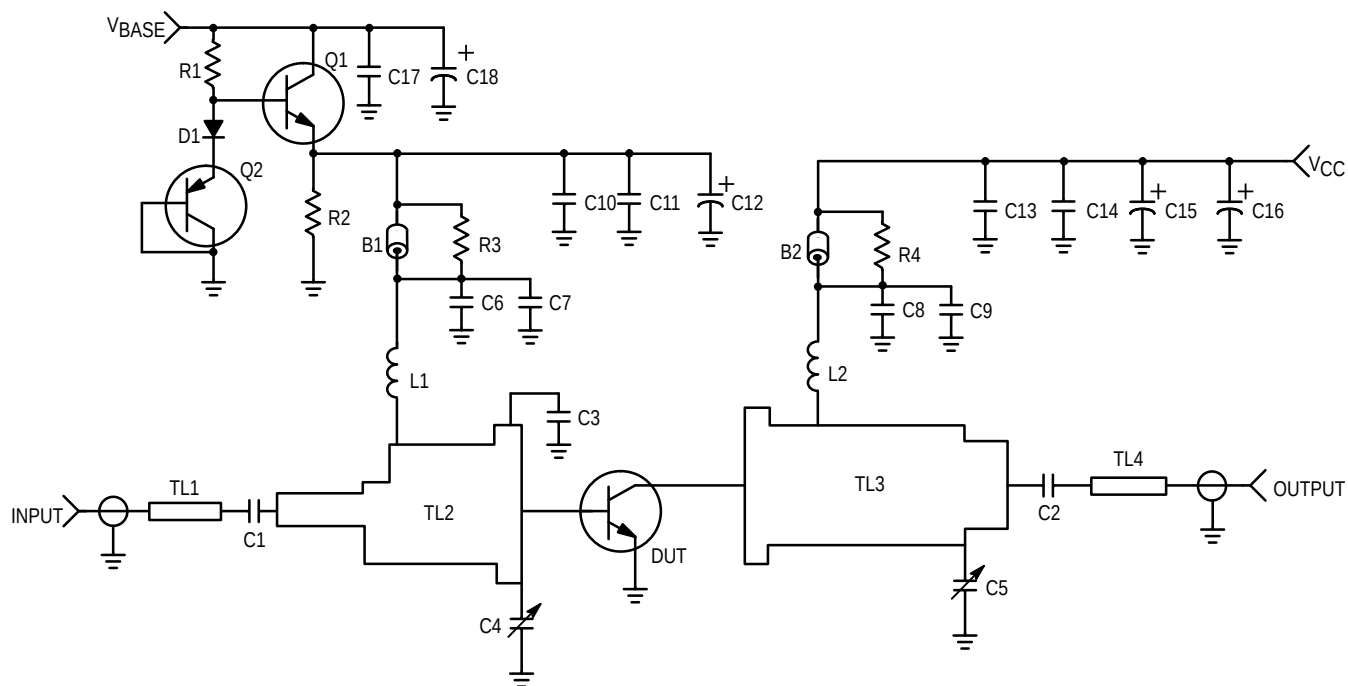
DYNAMIC CHARACTERISTICS

Output Capacitance ($V_{CB} = 26\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$) (1)	C_{ob}	—	55	—	pF
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FUNCTIONAL TESTS (In Motorola Test Circuit. See Figure 1)

Common–Emitter Amplifier Power Gain ($V_{CC} = 26\text{ Vdc}$, $P_{out} = 60\text{ Watts (PEP)}$, $I_{CQ} = 200\text{ mA}$, $f_1 = 1490.0\text{ MHz}$, $f_2 = 1490.1\text{ MHz}$)	G_{pe}	10	11.7	—	dB
Collector Efficiency ($V_{CC} = 26\text{ Vdc}$, $P_{out} = 60\text{ Watts (PEP)}$, $I_{CQ} = 200\text{ mA}$, $f_1 = 1490.0\text{ MHz}$, $f_2 = 1490.1\text{ MHz}$)	η	33	38	—	dB
3rd Order Intermodulation Distortion ($V_{CC} = 26\text{ Vdc}$, $P_{out} = 60\text{ Watts (PEP)}$, $I_{CQ} = 200\text{ mA}$, $f_1 = 1490.0\text{ MHz}$, $f_2 = 1490.1\text{ MHz}$)	IMD	—	– 32	– 28	dB
Input Return Loss ($V_{CC} = 26\text{ Vdc}$, $P_{out} = 60\text{ Watts (PEP)}$, $I_{CQ} = 200\text{ mA}$, $f_1 = 1490.0\text{ MHz}$, $f_2 = 1490.1\text{ MHz}$)	IRL	12	20	—	dB
Output Mismatch Stress ($V_{CC} = 26\text{ Vdc}$, $P_{out} = 60\text{ Watts (PEP)}$, $I_{CQ} = 200\text{ mA}$, $f_1 = 1490.0\text{ MHz}$, $f_2 = 1490.1\text{ MHz}$, VSWR = 3:1, at All Phase Angles)	ψ	No Degradation in Output Power			

(1) For information only. This part is collector matched.



B1, B2 Short RF Bead Fair Rite-2743019447
 C1, C2, C6, C8 18 pF, Chip Capacitor
 C3 3.9 pF, Chip Capacitor
 C4, C5 0.6–4.5 pF, Variable Capacitor
 C7, C9 100 pF, Chip Capacitor
 C10, C13 1000 pF, Chip Capacitor
 C11, C14, C17 0.1 μ F, 50 Vdc Ceramic Capacitor
 C12, C15, C18 10 μ F, 50 Vdc Electrolytic Capacitor
 C16 250 μ F, 50 Vdc Electrolytic Capacitor

D1 Diode, 1N4003
 L1, L2 3 Turns, 20 AWG, IDIA 0.102" (17.7 nH)
 Q1 Transistor, NPN BD135
 Q2 Transistor, PNP BD136
 R1 120 Ω , 1/4 W Resistor
 R2 51 Ω , 1/4 W, Chip Resistor
 R3, R4 4 x 39 Ω , 1/8 W Chip Resistors
 TL1–TL4 Microstrip Line See Photomaster
 Board 1/32" Glass Teflon®, Arlon GX-0300-55-22,
 $\epsilon_r = 2.55$

Figure 1. MRF15060 RF Test Fixture Schematic

TYPICAL CHARACTERISTICS

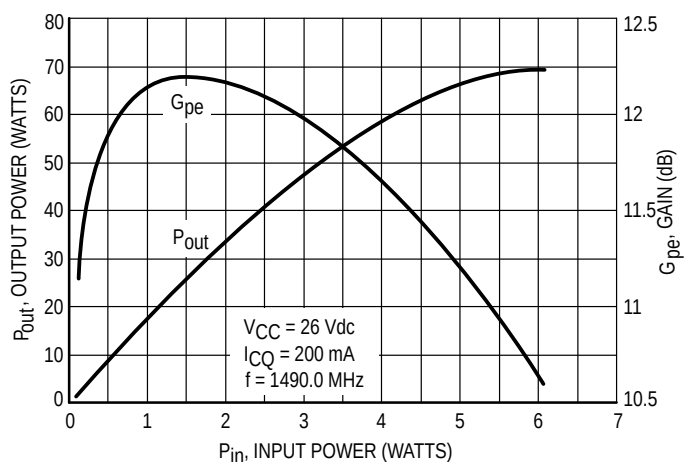


Figure 2. Output Power & Power Gain versus Input Power

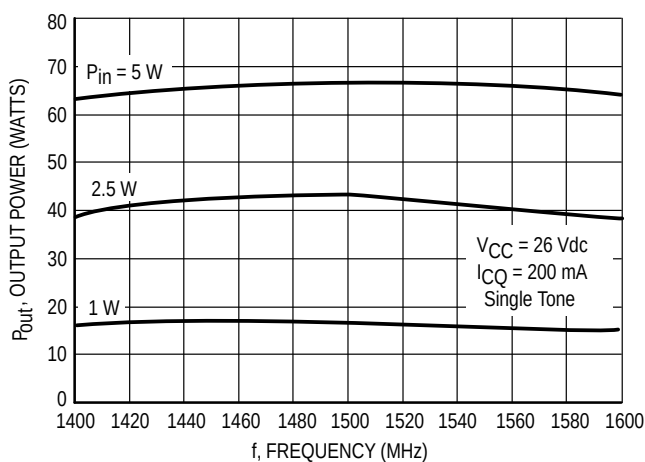


Figure 3. Output Power versus Frequency

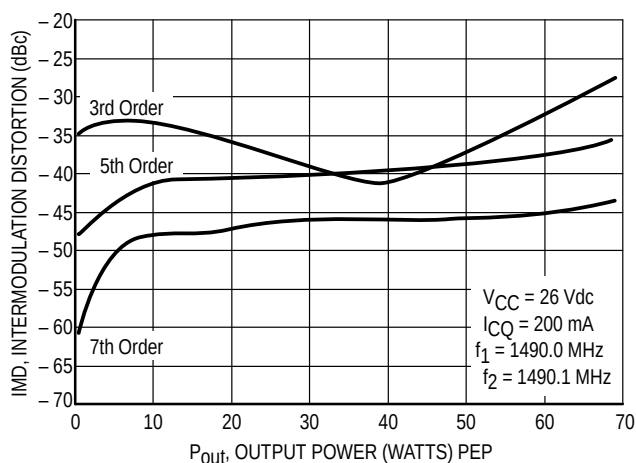


Figure 4. Intermodulation Distortion versus Output Power

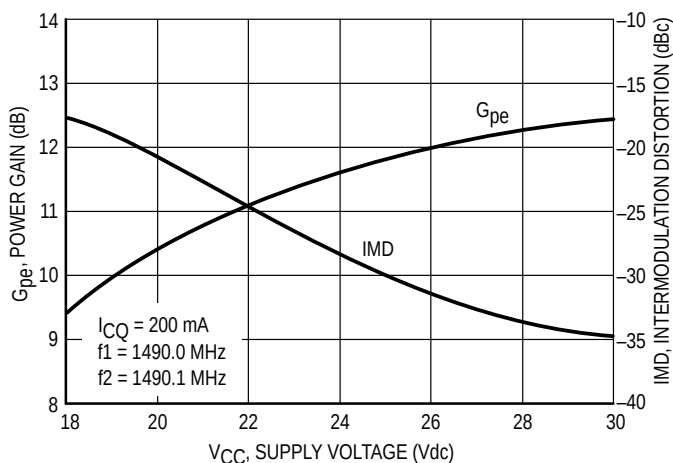


Figure 5. Power Gain and Intermodulation Distortion versus Supply Voltage

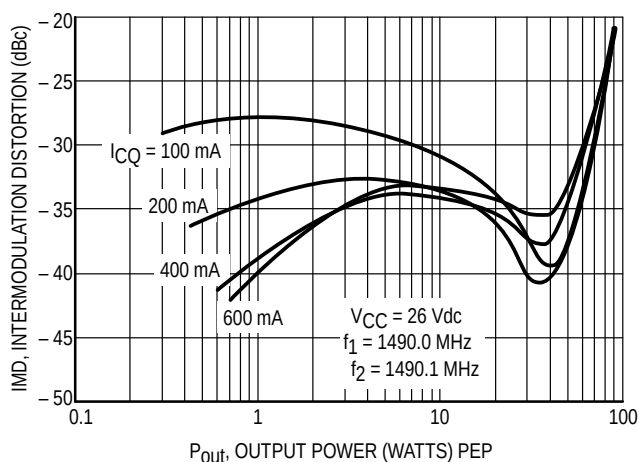


Figure 6. Intermodulation Distortion versus Output Power

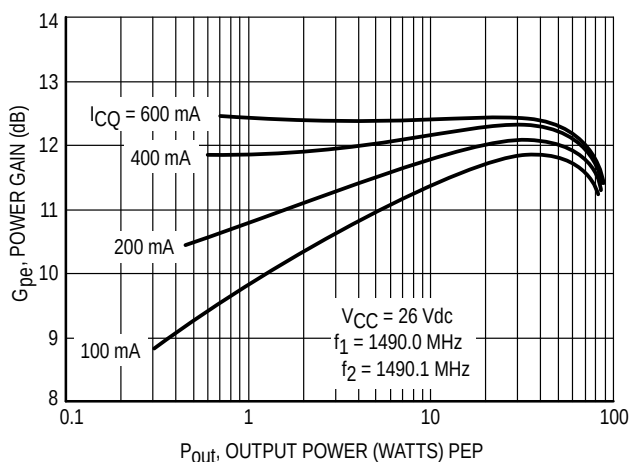


Figure 7. Power Gain versus Output Power

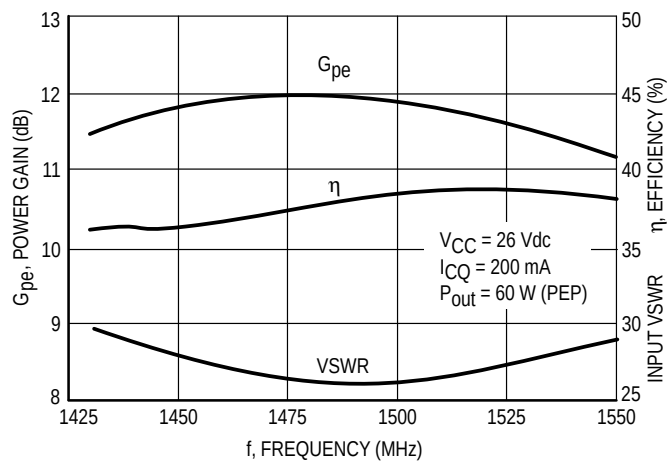


Figure 8. Performance in Broadband Circuit

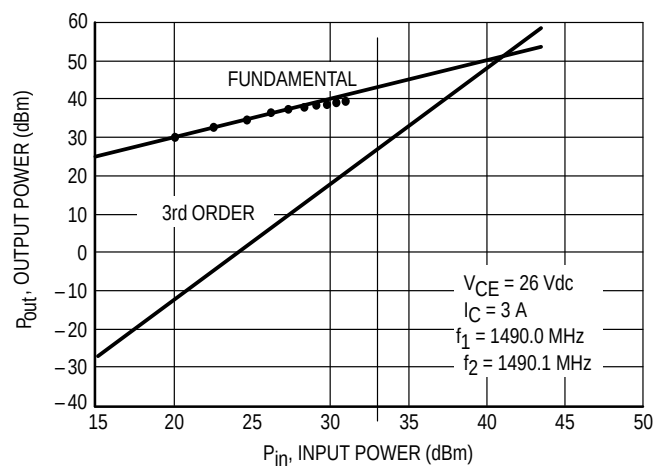


Figure 9. Class A Third Order Intercept Point

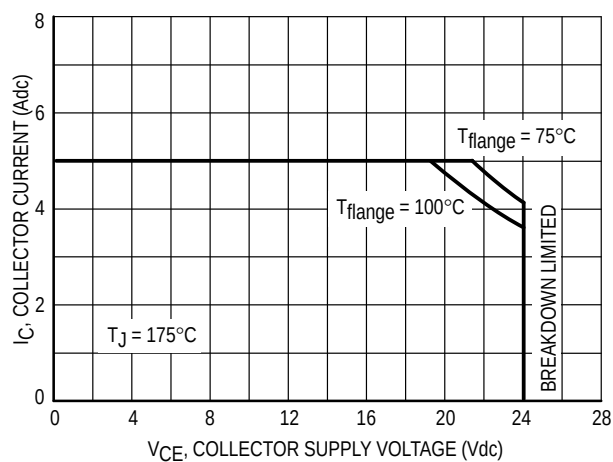
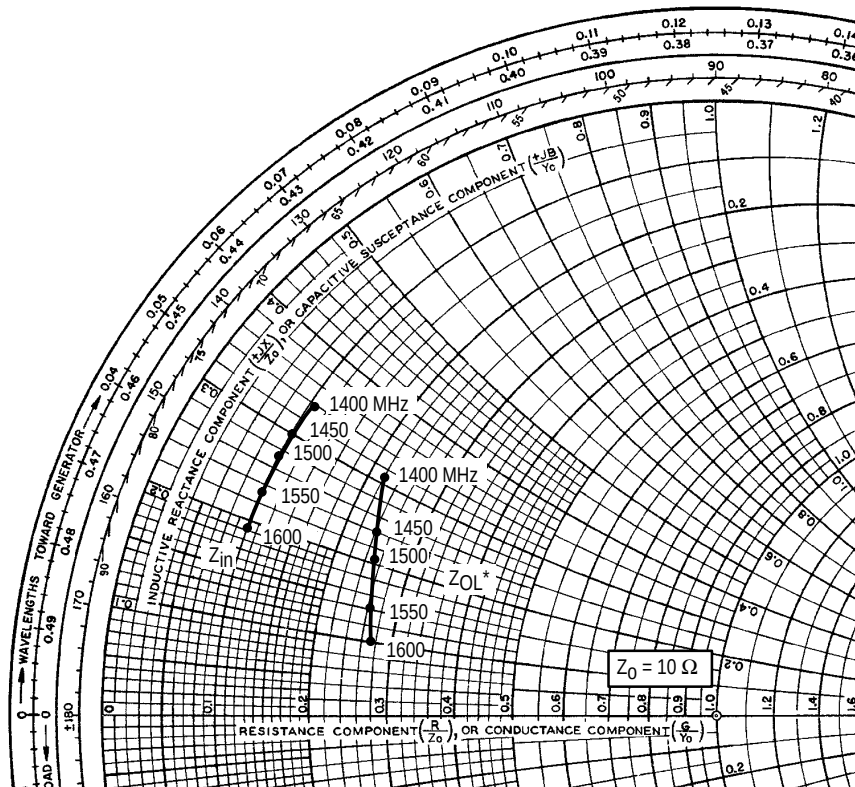


Figure 10. DC Safe Operating Area



$V_{CC} = 26 \text{ Vdc}$, $I_{CQ} = 200 \text{ mA}$, $P_{out} = 60 \text{ Watts PEP}$

f MHz	$Z_{in(1)}$ Ohms	Z_{OL}^* Ohms
1400	$1.07 + j3.4$	$2.25 + j3.1$
1450	$1.04 + j3.0$	$2.37 + j2.4$
1500	$1.01 + j2.7$	$2.46 + j2.1$
1550	$0.99 + j2.3$	$2.54 + j1.4$
1600	$0.97 + j1.9$	$2.66 + j1.0$

$Z_{in(1)} =$ Conjugate of fixture base impedance.

$Z_{OL}^* =$ Conjugate of the optimum load impedance at given output power, voltage, bias current and frequency.

Figure 11. Series Equivalent Input and Output Impedance

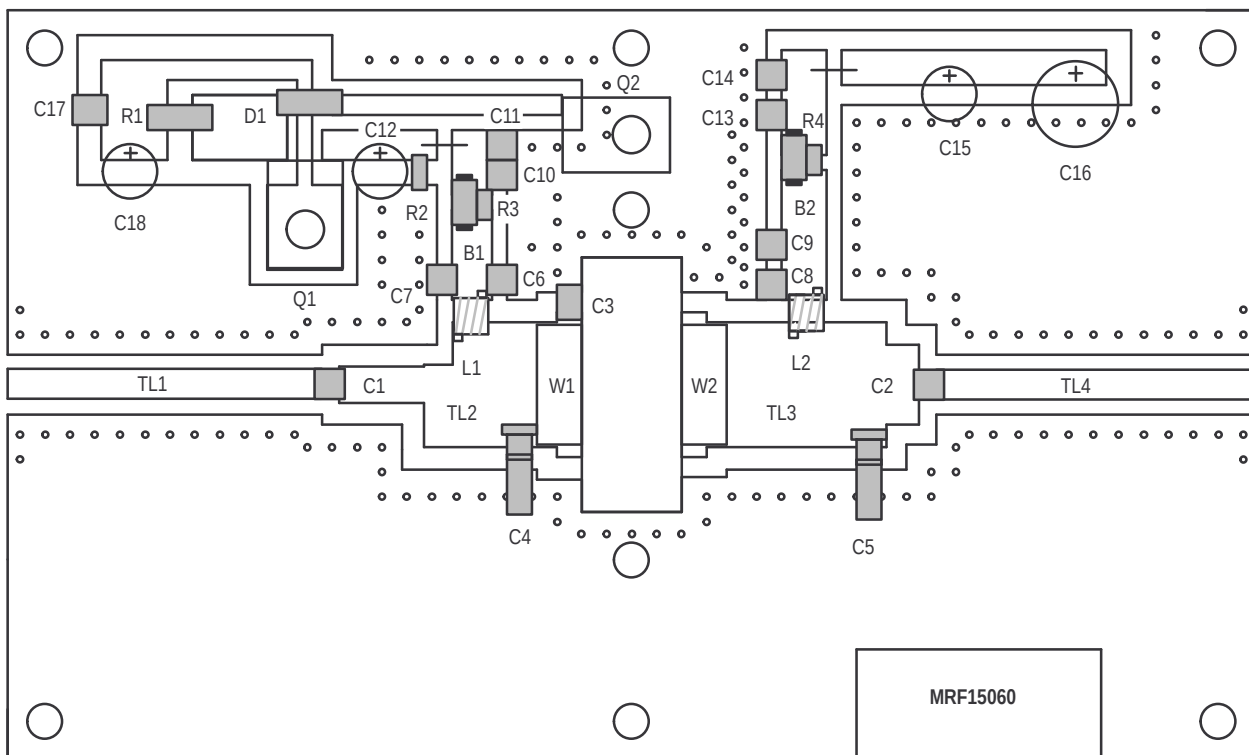


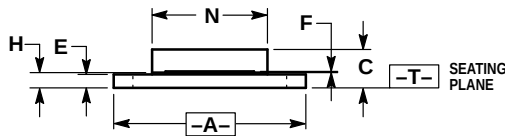
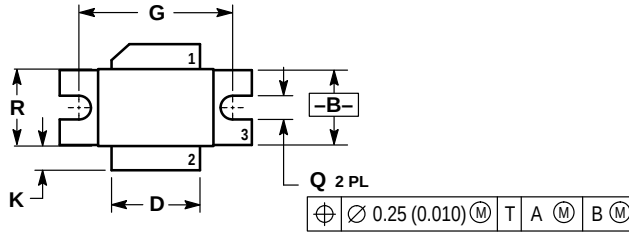
Figure 12. MRF15060 Component Parts Layout

Table 1. Typical Common Emitter S-Parameters ($V_{CC} = 26\text{ V}$)

$I_D = 3.0\text{ A}$

f MHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	S ₁₁	∠φ	S ₂₁	∠φ	S ₁₂	∠φ	S ₂₂	∠φ
1000	0.964	163	0.28	93	0.018	73	0.991	178
1050	0.958	162	0.30	87	0.018	76	0.989	178
1100	0.957	161	0.31	82	0.017	81	0.987	179
1150	0.956	160	0.34	76	0.022	73	0.982	179
1200	0.955	158	0.38	70	0.023	67	0.969	179
1250	0.953	157	0.42	62	0.022	57	0.956	180
1300	0.941	155	0.47	53	0.019	60	0.937	180
1350	0.922	154	0.55	43	0.015	64	0.915	-180
1400	0.920	153	0.67	28	0.013	66	0.891	-180
1450	0.901	152	0.80	6	0.012	71	0.880	-180
1500	0.903	151	0.83	-24	0.007	76	0.911	-179
1550	0.906	152	0.70	-54	0.008	89	0.954	-180
1600	0.913	153	0.51	-75	0.009	92	0.971	-180
1650	0.921	154	0.38	-89	0.010	95	0.973	-179
1700	0.946	154	0.29	-98	0.012	97	0.974	-179
1750	0.974	155	0.34	-107	0.014	105	0.976	-178
1800	0.968	154	0.19	-115	0.016	116	0.977	-178
1850	0.966	153	0.16	-121	0.018	138	0.978	-177
1900	0.947	152	0.14	-128	0.021	143	0.980	-177
1950	0.918	151	0.12	-138	0.027	151	0.982	-177
2000	0.912	150	0.09	-146	0.031	159	0.985	-176

PACKAGE DIMENSIONS

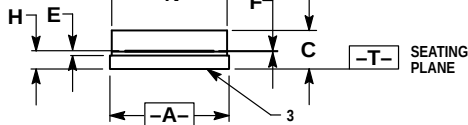
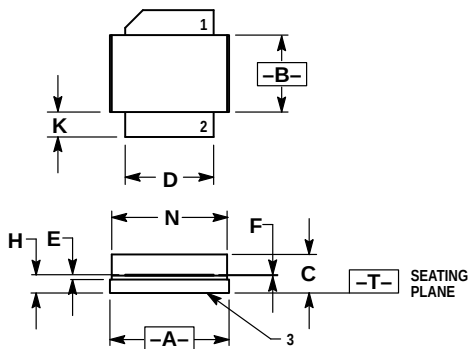


**CASE 451-04
ISSUE D**

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.995	1.005	25.27	25.53
B	0.380	0.390	9.65	9.91
C	0.170	0.205	4.32	5.21
D	0.455	0.465	11.56	11.81
E	0.060	0.075	1.52	1.91
F	0.004	0.006	0.10	0.15
G	0.800 BSC		20.32 BSC	
H	0.078	0.090	1.98	2.29
K	0.117	0.137	2.97	3.48
N	0.595	0.605	15.11	15.37
Q	0.120	0.130	3.05	3.30
R	0.395	0.410	10.03	10.41

- STYLE 1:
- PIN 1. COLLECTOR
 - BASE
 - EMITTER



**CASE 451A-01
ISSUE O**

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.615	0.625	15.62	15.88
B	0.395	0.410	10.03	10.41
C	0.170	0.205	4.32	5.21
D	0.455	0.465	11.56	11.81
E	0.060	0.075	1.52	1.91
F	0.004	0.006	0.10	0.15
H	0.078	0.090	1.98	2.29
K	0.117	0.137	2.97	3.48
N	0.595	0.605	15.11	15.37

- STYLE 1:
- PIN 1. COLLECTOR
 - BASE
 - EMITTER

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